

Three Phase Rectifier Bridges Slim Version

PSDS 192

I_{dAV}

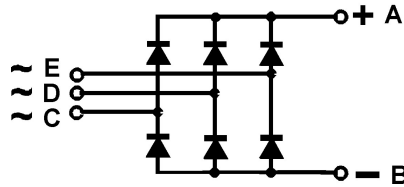
= 248 A

V_{RRM}

= 800-1800 V

Preliminary Data Sheet

V_{RSM} V	V_{RRM} V	Type
800	800	PSDS 192/08
1200	1200	PSDS 192/12
1400	1400	PSDS 192/14
1600	1600	PSDS 192/16
1800	1800	PSDS 192/18



Symbol	Test Conditions			Maximum Ratings	
I_{dAV}	$T_C = 90^\circ\text{C}$, module			248	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$	$t = 10\text{ ms}$	(50 Hz), sine	2800	A
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	3300	A
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$	(50 Hz), sine	2500	A
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	2750	A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$	$t = 10\text{ ms}$	(50 Hz), sine	39200	$\text{A}^2\text{ s}$
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	45000	$\text{A}^2\text{ s}$
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$	(50 Hz), sine	31200	$\text{A}^2\text{ s}$
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	31200	$\text{A}^2\text{ s}$
T_{VJ}				-40 ... + 150	$^\circ\text{C}$
T_{VJM}				150	$^\circ\text{C}$
T_{stg}				-40 ... + 125	$^\circ\text{C}$
V_{ISOL}	50/60 HZ, RMS	$t = 1\text{ min}$		2500	V ~
	$I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ s}$		3000	V ~
M_d	Mounting torque	(M6)		5	Nm
	Terminal connection torque	(M6)		5	Nm
Weight	typ.			225	g

Features

- Low profile (overall height: 17 mm)
- Package with screw terminals
- Isolation voltage 3000 V~
- Planar glasspassivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL release applied, RoHS conform

Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

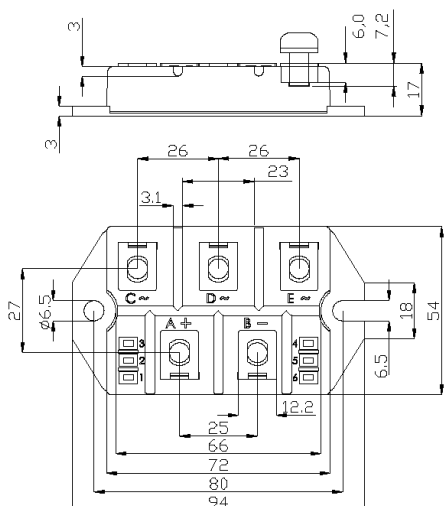
Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability

Package, style and outline

Dimensions in mm (1mm = 0.0394")

Max. allowed screw-in depth: 7.2 mm



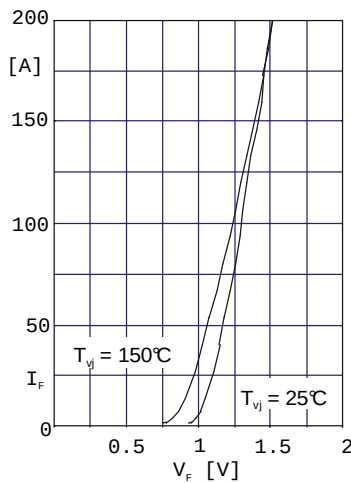


Fig. 1 Forward current versus voltage drop per diode

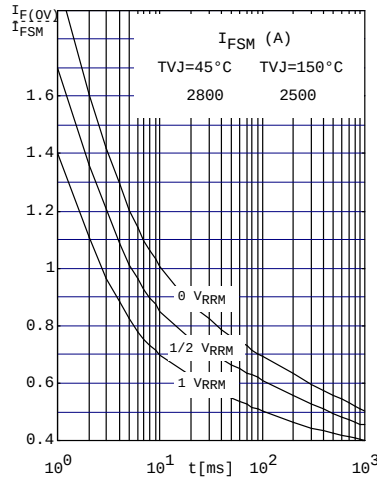


Fig. 2 Surge overload current per diode I_{FSM} : Crest value.
t: duration

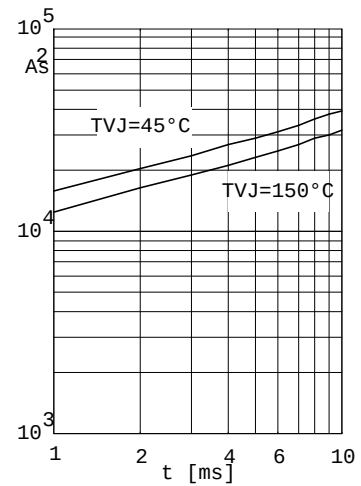


Fig. 3 $\int i^2 dt$ versus time (1-10ms) per diode (or thyristor)

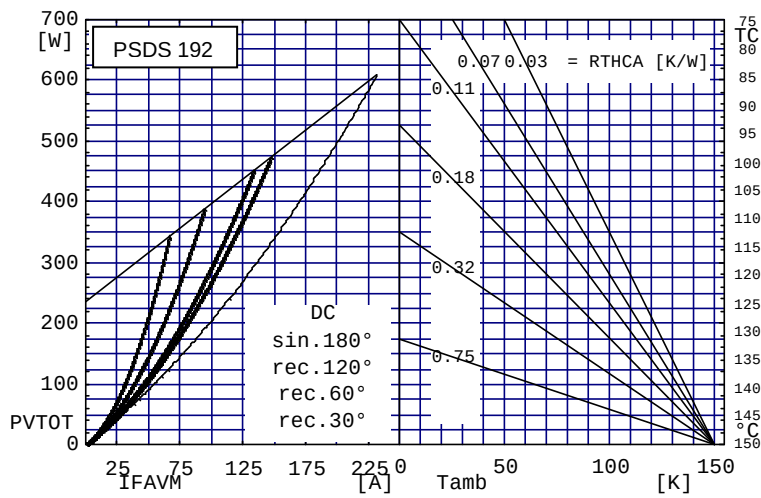


Fig. 4 Power dissipation versus direct output current and ambient temperature

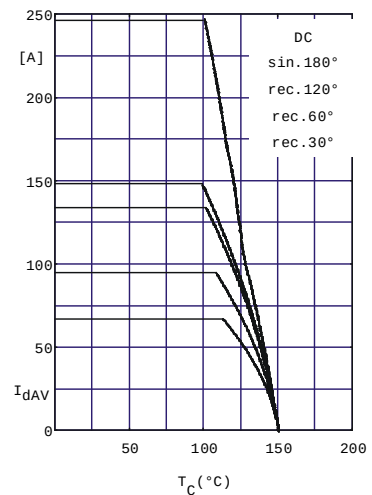


Fig.5 Maximum forward current at case temperature

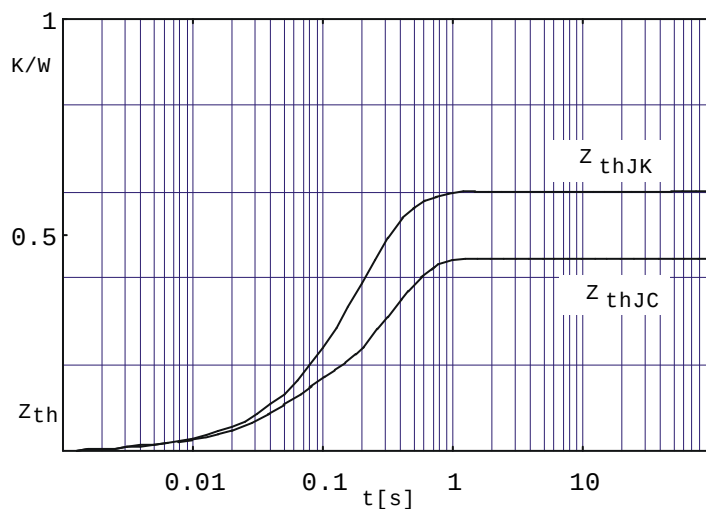


Fig. 6 Transient thermal impedance per diode (or thyristor), calculated